

## Dual N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY			
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>a</sup>	$Q_g$ (Typ.)
30	0.020 at $V_{GS} = 10$ V	6.5	7.1
	0.025 at $V_{GS} = 4.5$ V	5.5	

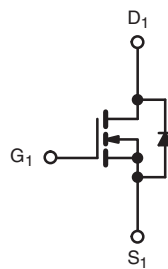
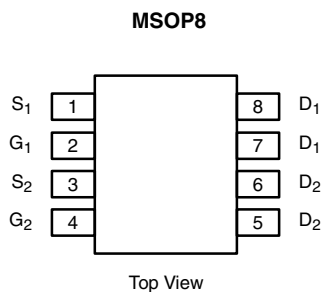
### FEATURES

- Trench Power MOSFET
- 100 %  $R_g$  Tested
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC

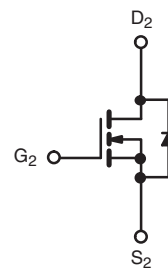

**RoHS**  
 COMPLIANT

### APPLICATIONS

- Notebook System Power
- Low Current DC/DC



N-Channel MOSFET



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	$V_{DS}$	30	V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$		
Continuous Drain Current ( $T_J = 150$ °C)	$I_D$	$T_C = 25$ °C	6.5	
		$T_C = 70$ °C	4.5	
		$T_A = 25$ °C	2.2 <sup>b, c</sup>	
		$T_A = 70$ °C	1.0 <sup>b, c</sup>	
Pulsed Drain Current	$I_{DM}$	26	A	
Source-Drain Current Diode Current	$I_S$	$T_C = 25$ °C		2.8
		$T_A = 25$ °C		1.8 <sup>b, c</sup>
Pulsed Source-Drain Current	$I_{SM}$	30		
Single Pulse Avalanche Current	$L = 0.1$ mH	$I_{AS}$		10
Single Pulse Avalanche Energy		$E_{AS}$		5
Maximum Power Dissipation	$P_D$	$T_C = 25$ °C	3.1	
		$T_C = 70$ °C	2.0	
		$T_A = 25$ °C	2.0 <sup>b, c</sup>	
		$T_A = 70$ °C	1.25 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typ.	Max.	Unit
Maximum Junction-to-Ambient <sup>b, d</sup>	$t \leq 10$ s	$R_{thJA}$	52	62.5	°C/W
Maximum Junction-to-Foot (Drain)	Steady-State	$R_{thJF}$	30	40	

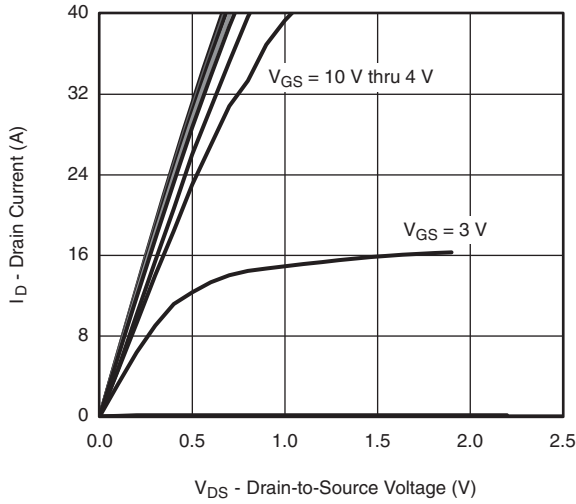
Notes:

- Based on  $T_C = 25$  °C.
- Surface mounted on 1" x 1" FR4 board.
- $t = 10$  s.
- Maximum under steady state conditions is 110 °C/W.

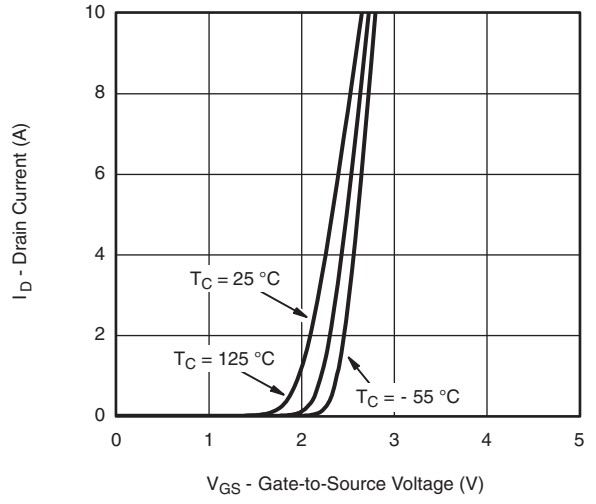
<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		3.0		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250\text{ }\mu\text{A}$		-5.2		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.2		2.5	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			100	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On -State Drain Current <sup>b</sup>	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	20			A
Drain-Source On-State Resistance <sup>b</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 3\text{ A}$		0.020		$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 2\text{ A}$		0.025		
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 6\text{ A}$		27		S
<b>Dynamic<sup>a</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, I_D = 1\text{ MHz}$		800		pF
Output Capacitance	$C_{oss}$			140		
Reverse Transfer Capacitance	$C_{rss}$			86		
Total Gate Charge	$Q_g$	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 6\text{ A}$		14.5	22	nC
				7.1	11	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 6\text{ A}$		1.9		
Gate-Drain Charge	$Q_{gd}$			2.7		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$	0.5	2.6	5.2	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 3\text{ }\Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		14	28	ns
Rise Time	$t_r$			45	80	
Turn-Off Delay Time	$t_{d(off)}$			18	35	
Fall Time	$t_f$			12	24	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 3\text{ }\Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		7	14	
Rise Time	$t_r$			10	20	
Turn-Off Delay Time	$t_{d(off)}$			15	30	
Fall Time	$t_f$			7	14	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			6.5	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				26	
Body Diode Voltage	$V_{SD}$	$I_S = 2\text{ A}$		0.77	1.1	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 5\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		17	34	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			9	18	nC
Reverse Recovery Fall Time	$t_a$			10		nS
Reverse Recovery Rise Time	$t_b$			7		

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

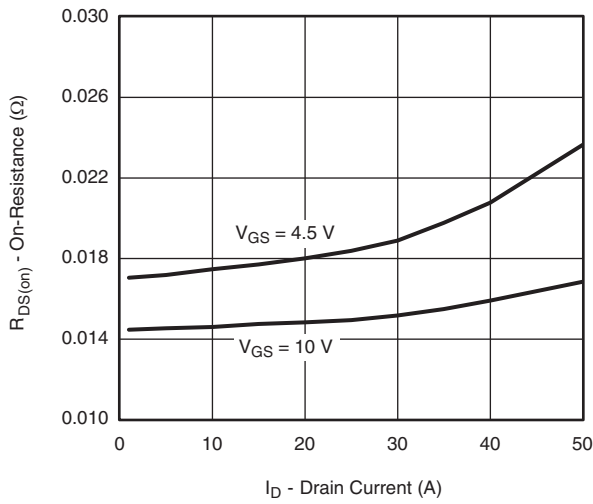
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



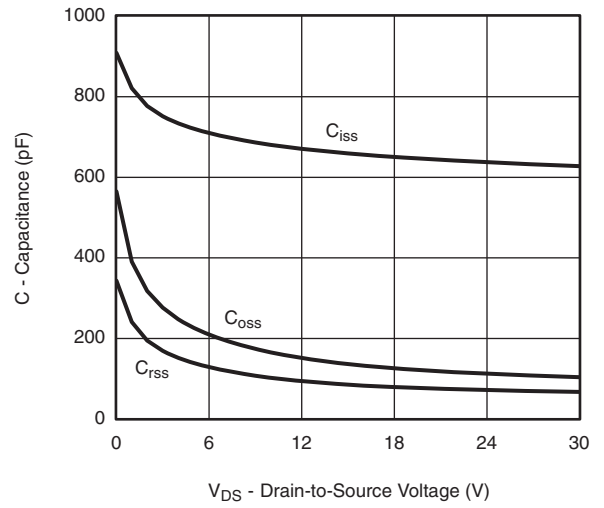
**Output Characteristics**



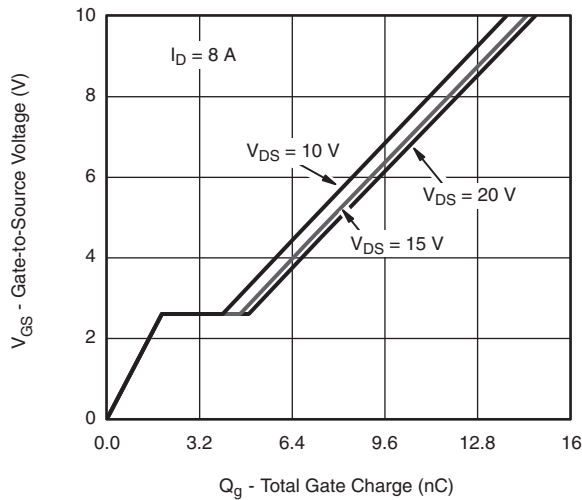
**Transfer Characteristics**



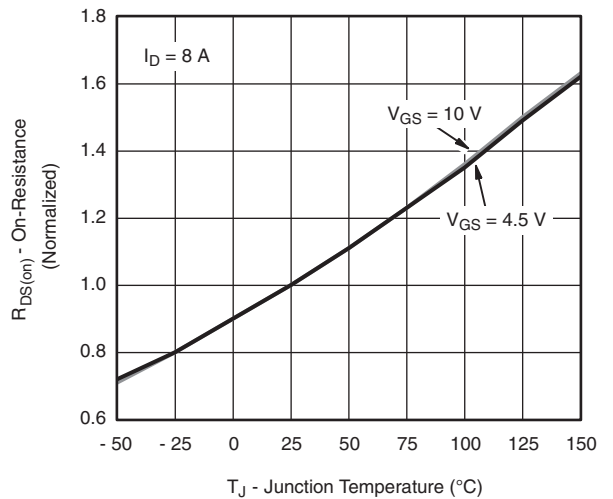
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**

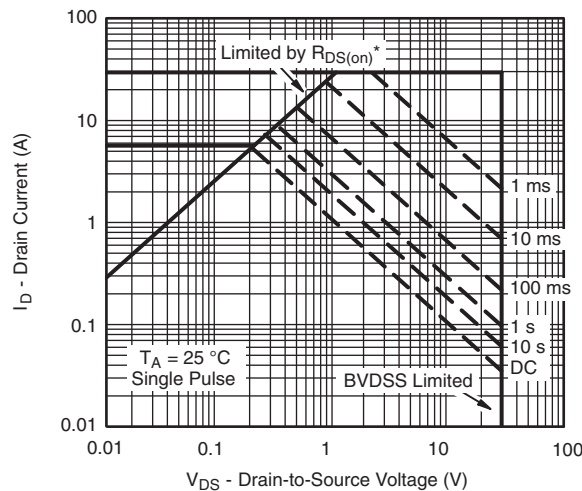
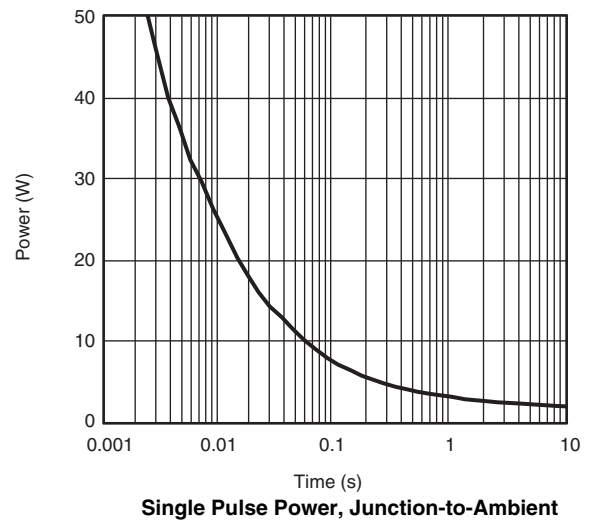
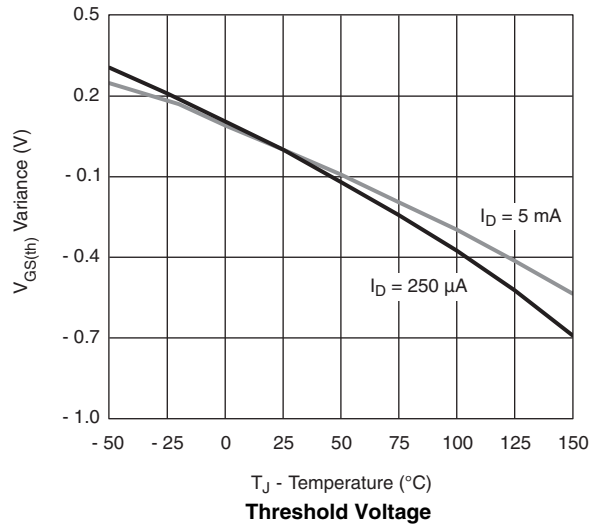
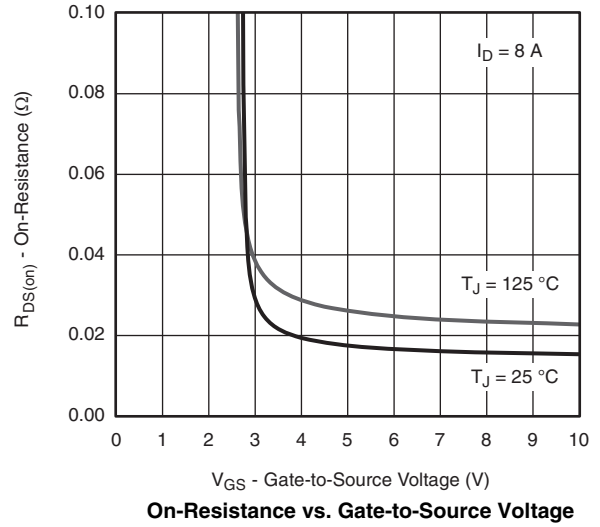
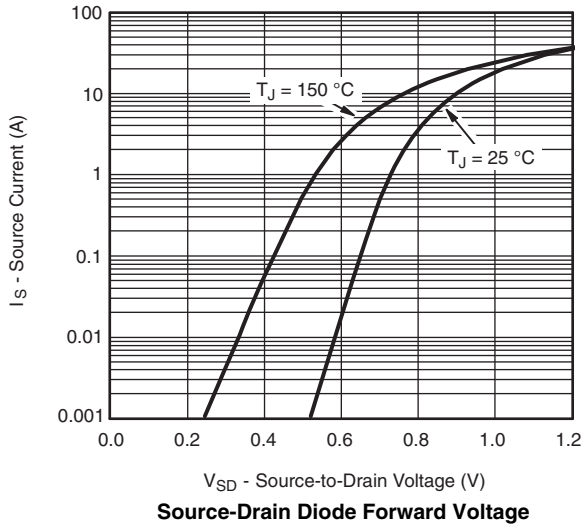


**Gate Charge**



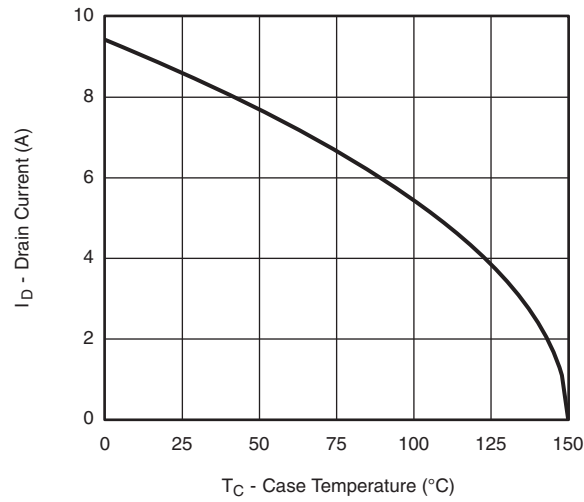
**On-Resistance vs. Junction Temperature**

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

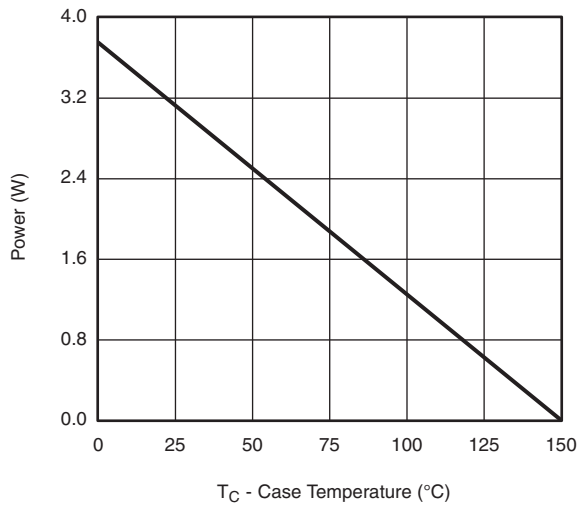


\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

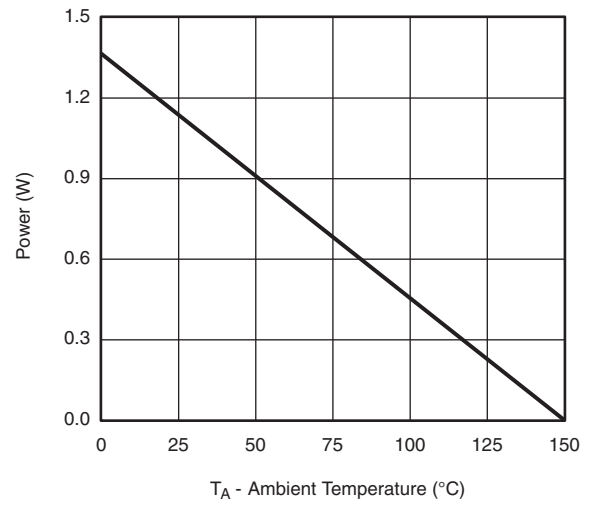
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Current Derating\***



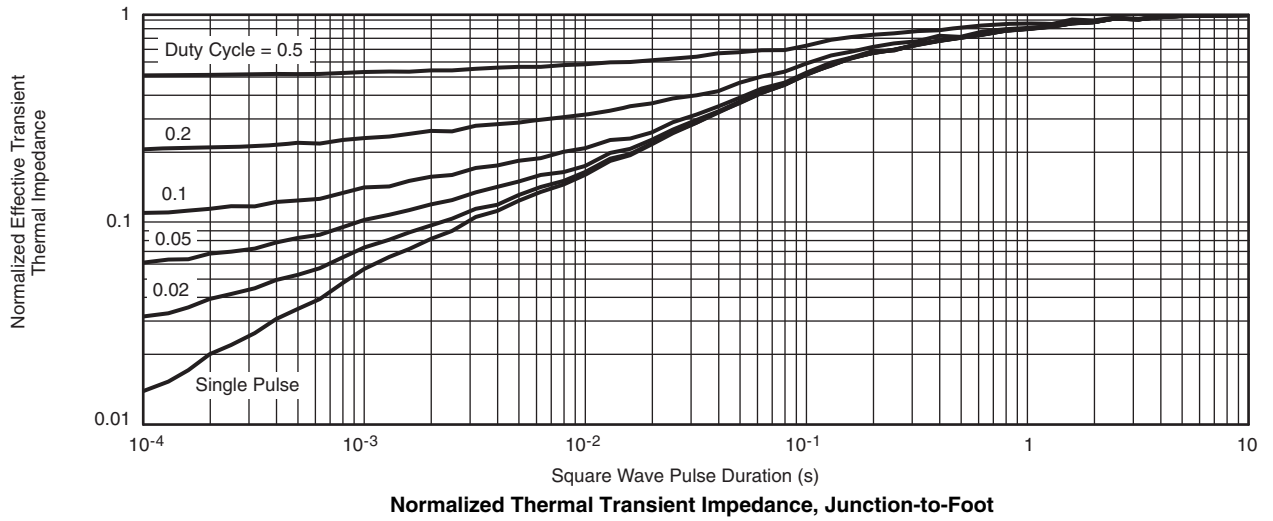
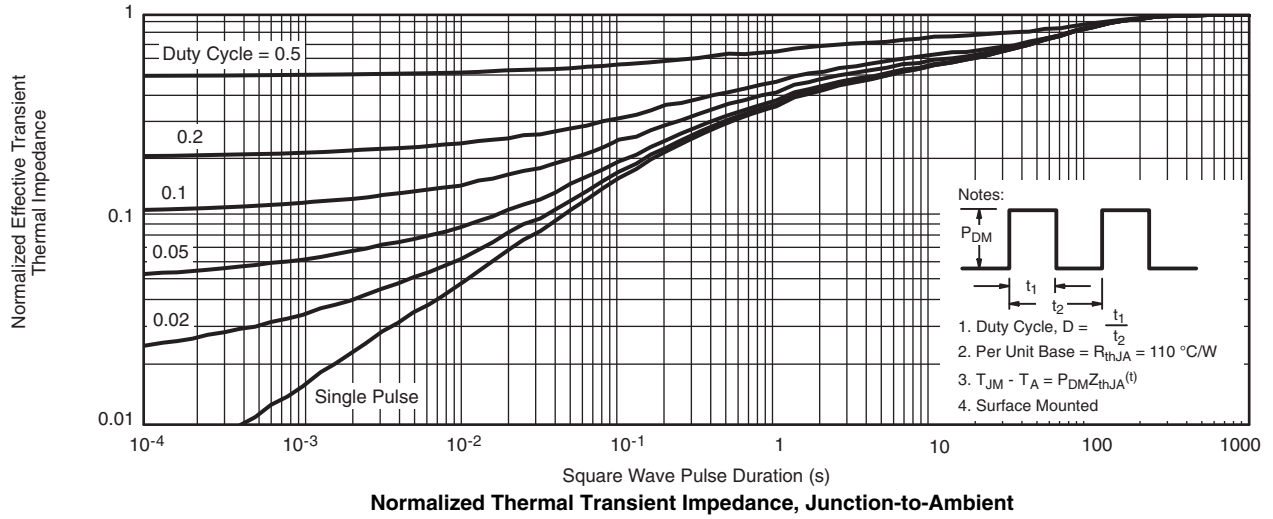
**Power Derating, Junction-to-Foot**



**Power Derating, Junction-to-Ambient**

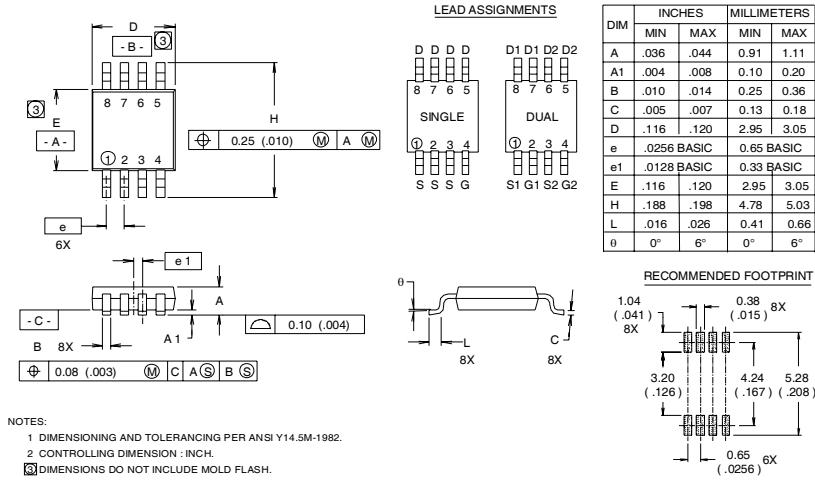
\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



# MSOP8 Package Outline

Dimensions are shown in millimeters (inches)



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